# **BC847 series**

# 45 V, 100 mA NPN general-purpose transistors Rev. 8 — 20 August 2012

Product data sheet

#### 1. **Product profile**

### 1.1 General description

NPN general-purpose transistors in Surface-Mounted Device (SMD) plastic packages.

Table 1. **Product overview** 

Type number[1]	Package	PNP complement		
	NXP	JEITA	JEDEC	
BC847	SOT23	-	TO-236AB	BC857
BC847A				BC857A
BC847B				BC857B
BC847C				BC857C
BC847W	SOT323	OT323 SC-70	-	BC857W
BC847AW				BC857AW
BC847BW				BC857BW
BC847CW				BC857CW
BC847T	SOT416	SC-75	-	BC857T
BC847AT				BC857AT
BC847BT				BC857BT
BC847CT				BC857CT
BC847AM	SOT883	SC-101	-	BC857AM
BC847BM				BC857BM
BC847CM				BC857CM

<sup>[1]</sup> Valid for all available selection groups.

### 1.2 Features and benefits

- General-purpose transistors
- SMD plastic packages
- Three different gain selections

## 1.3 Applications

General-purpose switching and amplification



## 1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{CEO}$	collector-emitter voltage	open base	-	-	45	V
I <sub>C</sub>	collector current		-	-	100	mA
h <sub>FE</sub>	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 2 \text{ mA}$	110	-	800	
	h <sub>FE</sub> group A	rrent gain V <sub>CE</sub> = 5 V; I <sub>C</sub> = 2 mA 110 - 800 group A 110 180 220	220			
	h <sub>FE</sub> group B		200	290	450	
	h <sub>FE</sub> group C		420	520	800	

# 2. Pinning information

Table 3. Pinning

Table 3.	Pinning		
Pin	Description	Simplified outline	Graphic symbol
SOT23, S	OT323, SOT416		
1	base		•
2	emitter	[3]	3
3	collector	1 2 006aaa144	12 sym021
SOT883			
1	base		•
2	emitter	1 3	3
3	collector	2 Transparent top view	1 — 2 sym021

# 3. Ordering information

Table 4. Ordering information

Type number[1]	Package				
	Name	Description	Version		
BC847	-	plastic surface-mounted package; 3 leads	SOT23		
BC847A					
BC847B					
BC847C					
BC847W	SC-70	plastic surface-mounted package; 3 leads	SOT323		
BC847AW					
BC847BW					
BC847CW					
BC847T	SC-75	plastic surface-mounted package; 3 leads	SOT416		
BC847AT					
BC847BT					
BC847CT					
BC847AM	SC-101	leadless ultra small plastic package; 3 solder lands;	SOT883		
BC847BM		body $1.0 \times 0.6 \times 0.5 \text{ mm}$			
BC847CM					

<sup>[1]</sup> Valid for all available selection groups.

# 4. Marking

Table 5. Marking codes

Type number	Marking code <sup>[1]</sup>	Type number	Marking code <sup>[1]</sup>
BC847	1H*	BC847T	1N
BC847A	1E*	BC847AT	1E
BC847B	1F*	BC847BT	1F
BC847C	1G*	BC847CT	1G
BC847W	1H*	BC847AM	D4
BC847AW	1E*	BC847BM	D5
BC847BW	1F*	BC847CM	D6
BC847CW	1G*		

<sup>[1] \* =</sup> placeholder for manufacturing site code

# 5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CBO}$	collector-base voltage	open emitter	-	50	V
$V_{CEO}$	collector-emitter voltage	open base	-	45	V
$V_{EBO}$	emitter-base voltage	open collector	-	6	V
I <sub>C</sub>	collector current		-	100	mA
I <sub>CM</sub>	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	200	mA
I <sub>BM</sub>	peak base current	single pulse; $t_p \le 1 \text{ ms}$	-	100	mA
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25  ^{\circ}C$	<u>[1]</u>		
	SOT23		-	250	mW
	SOT323		-	200	mW
	SOT416		-	150	mW
	SOT883		[2]	250	mW
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		-65	+150	°C
T <sub>stg</sub>	storage temperature		-65	+150	°C

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

## 6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	<u>[1]</u>			
	SOT23		-	-	500	K/W
	SOT323		-	-	625	K/W
	SOT416		-	-	833	K/W
	SOT883		[2] _	-	500	K/W

<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

<sup>[2]</sup> Device mounted on an FR4 PCB with 60  $\mu m$  copper strip line, standard footprint.

<sup>[2]</sup> Device mounted on an FR4 PCB with 60  $\mu m$  copper strip line, standard footprint.

# 7. Characteristics

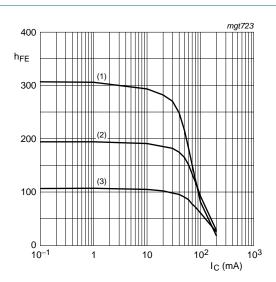
Table 8. Characteristics

 $T_{amb} = 25$  °C unless otherwise specified.

	C unless otherwise spe						
Symbol	Parameter	Conditions	N	Vlin	Тур	Max	Unit
$I_{CBO}$	collector-base cut-off	$V_{CB} = 30 \text{ V}; I_{E} = 0 \text{ A}$	-		-	15 n/ 5 µ/ 100 n/ 100 n	nA
	current	$V_{CB} = 30 \text{ V}; I_E = 0 \text{ A};$ $T_j = 150 \text{ °C}$	-		-		μΑ
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}$	-		-	100	nA
h <sub>FE</sub>	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 10 \mu\text{A}$					
	h <sub>FE</sub> group A		-		90	-	
	h <sub>FE</sub> group B		-	5 μA  100 nA  - 90 150 150 270 - 110 180 220 200 290 450 420 520 800 - 90 200 mV 1 - 200 400 mV 2 - 700 - mV 2 - 700 - mV 2 - 770 mV 100 - 770 mV 100 - MH  - 1.5 pF			
	h <sub>FE</sub> group C		-		270	- 15 nA - 5 μA - 100 nA - 100 nA - 100 nA - 150 - 270 - 800 - 800 - 180 220 - 290 450 - 520 800 - 90 200 mV - 700 - mV - 770 mV - MH: - 1.5 pF - 11 - pF	
	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 2 \text{ mA}$	1	- 90 150 110 - 800 - 110 180 220 200 290 450 420 520 800 - 90 200 mV - 200 400 mV - 700 - mV 580 660 700 mV - 770 mV			
	DC current gain $V_{CE} = 5 \text{ V}; I_{C} = 2 \text{ mA}$ $\begin{array}{c} h_{FE} \text{ group A} \\ h_{FE} \text{ group B} \\ \hline \\ h_{FE} \text{ group C} \\ \hline \\ V_{CEsat} \end{array}$ $\begin{array}{c} collector\text{-emitter} \\ saturation voltage \\ \hline \\ V_{BEsat} \end{array}$ $\begin{array}{c} l_{C} = 10 \text{ mA}; l_{B} = 0.5 \text{ mA} \\ l_{C} = 100 \text{ mA}; l_{B} = 5 \text{ mA} \\ \hline \\ l_{C} = 10 \text{ mA}; l_{B} = 0.5 \text{ mA} \\ \hline \\ l_{C} = 10 \text{ mA}; l_{C} = 10$	1	110	180	220		
	h <sub>FE</sub> group B	110 180 220 200 290 450 420 520 800 I <sub>C</sub> = 10 mA; I <sub>B</sub> = 0.5 mA - 90 200					
	h <sub>FE</sub> group C		4	420 520 800			
$V_{\text{CEsat}}$		$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}$	-		90	0 800 200 mV 0 400 mV	mV
	saturation voltage	$I_C = 100 \text{ mA}; I_B = 5 \text{ mA}$			520       800         90       200       mV         200       400       mV         700       -       mV	mV	
$V_{BEsat}$		$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}$	[2]		700	15 nA 5 μA 100 nA 100 - mN 100 400 mN 100 - mN 100 - mN 11.5 pF 11.5 pF	mV
	saturation voltage	$I_C = 100 \text{ mA}; I_B = 5 \text{ mA}$	[2]		900		mV
$V_{BE}$	base-emitter voltage	$I_C = 2 \text{ mA}; V_{CE} = 5 \text{ V}$	[2] 5	580	660	15 nA 5 μA 100 nA 100	mV
		$I_C$ = 10 mA; $V_{CE}$ = 5 V	-		-	770	mV
f <sub>T</sub>	transition frequency	$V_{CE} = 5 \text{ V}; I_{C} = 10 \text{ mA};$ f = 100 MHz	1	100	-	-	MHz
C <sub>c</sub>	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz	-		-	1.5	pF
C <sub>e</sub>	emitter capacitance	$V_{EB} = 0.5 \text{ V}; I_C = I_c = 0 \text{ A};$ f = 1 MHz	-		11	-	pF
NF	noise figure	$I_C$ = 200 μA; $V_{CE}$ = 5 V; $R_S$ = 2 kΩ; f = 1 kHz; B = 200 Hz	-		2	10	dB

<sup>[1]</sup> Pulse test:  $t_p \le 300~\mu s;~\delta = 0.02.$ 

<sup>[2]</sup>  $V_{BE}$  decreases by approximately 2 mV/K with increasing temperature.



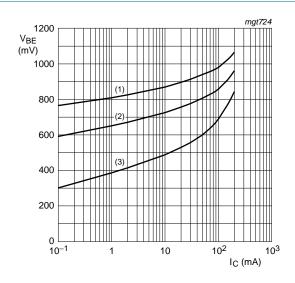
$$V_{CE} = 5 V$$

(1) 
$$T_{amb} = 150 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3)  $T_{amb} = -55 \, ^{\circ}C$ 

Group A: DC current gain as a function of Fig 1. collector current; typical values



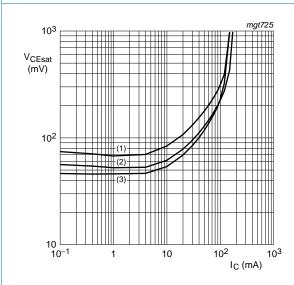
$$V_{CE} = 5 V$$

(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3)  $T_{amb} = 150 \, ^{\circ}C$ 

Group A: Base-emitter voltage as a function of Fig 2. collector current; typical values



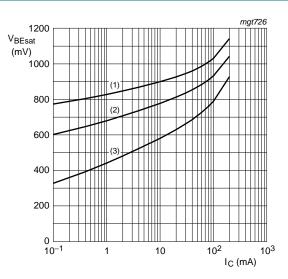
$$I_{\rm C}/I_{\rm B} = 20$$

(1) 
$$T_{amb} = 150 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = -55 \, ^{\circ}C$$

Fig 3. **Group A: Collector-emitter saturation voltage** as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B} = 10$$

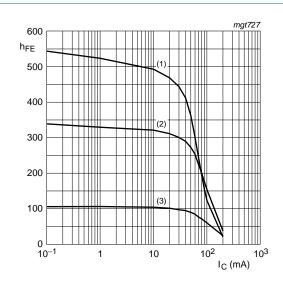
(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3)  $T_{amb} = 150 \, ^{\circ}C$ 

Fig 4. Group A: Base-emitter saturation voltage as a function of collector current; typical values

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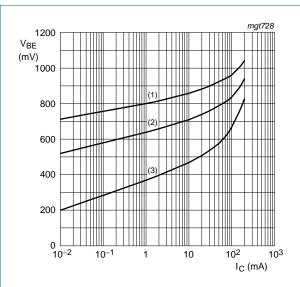
$$V_{CE} = 5 V$$

(1) 
$$T_{amb} = 150 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3)  $T_{amb} = -55 \, ^{\circ}C$ 

Fig 5. Group B: DC current gain as a function of collector current; typical values



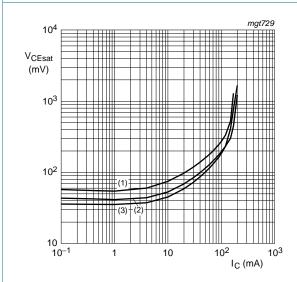
$$V_{CE} = 5 V$$

(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3)  $T_{amb} = 150 \, ^{\circ}C$ 

Fig 6. Group B: Base-emitter voltage as a function of collector current; typical values



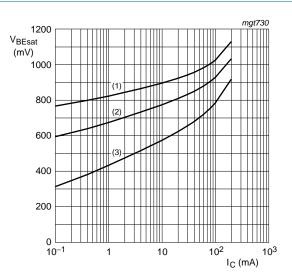
 $I_{\rm C}/I_{\rm B} = 20$ 

(1) 
$$T_{amb} = 150 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3)  $T_{amb} = -55 \, ^{\circ}C$ 

Fig 7. Group B: Collector-emitter saturation voltage as a function of collector current; typical values



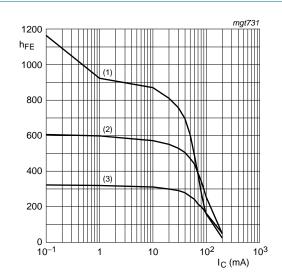
 $I_{\rm C}/I_{\rm B} = 10$ 

(1) 
$$T_{amb} = -55 \,^{\circ}C$$

(2)  $T_{amb} = 25 \, ^{\circ}C$ 

(3)  $T_{amb} = 150 \, ^{\circ}C$ 

Fig 8. Group B: Base-emitter saturation voltage as a function of collector current; typical values



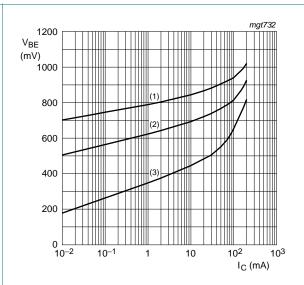
$$V_{CE} = 5 V$$

(1) 
$$T_{amb} = 150 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = -55 \, ^{\circ}C$$

Fig 9. Group C: DC current gain as a function of collector current; typical values



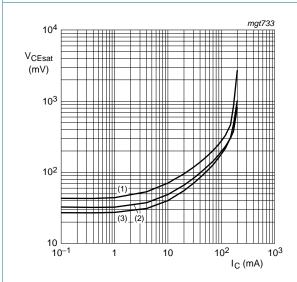
$$V_{CE} = 5 V$$

(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = 150 \, ^{\circ}C$$

Fig 10. Group C: Base-emitter voltage as a function of collector current; typical values



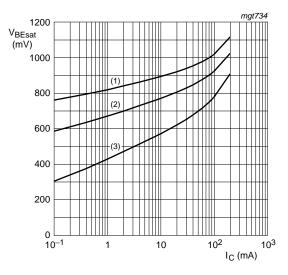
$$I_{\rm C}/I_{\rm B} = 20$$

(1) 
$$T_{amb} = 150 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = -55 \, ^{\circ}C$$

Fig 11. Group C: Collector-emitter saturation voltage as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B} = 10$$

(1) 
$$T_{amb} = -55 \,^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = 150 \, ^{\circ}C$$

Fig 12. Group C: Base-emitter saturation voltage as a function of collector current; typical values

**⊕** 04-11-04

# 8. Package outline

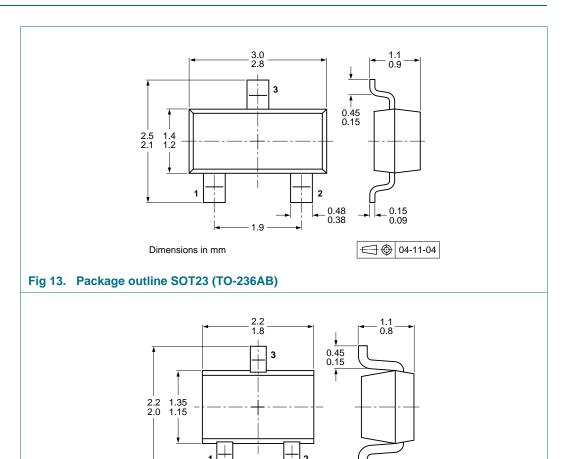
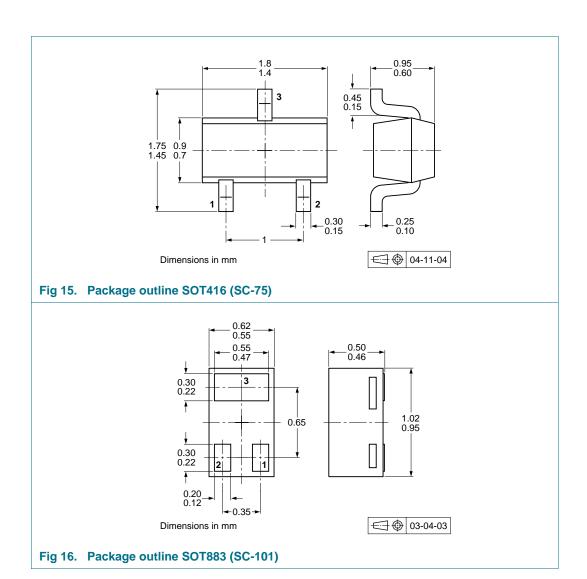


Fig 14. Package outline SOT323 (SC-70)

Dimensions in mm



# 9. Packing information

Table 9. Packing methods

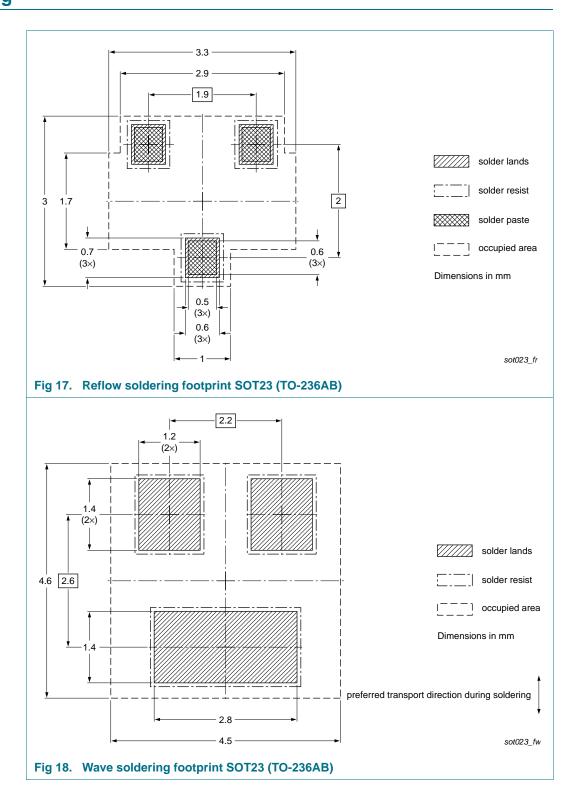
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

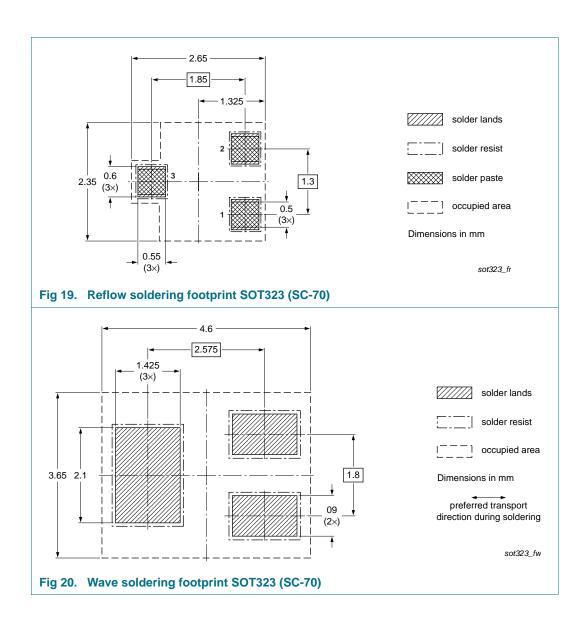
Type	Package	Description	Packing quantity		
number[2]			m pitch, 8 mm tape and reel -215 - m pitch, 8 mm tape and reel -115 - m pitch, 8 mm tape and reel -115 -	10000	
BC847	SOT23	4 mm pitch, 8 mm tape and reel	-215	-	-235
BC847A					
BC847B					
BC847C					
BC847W	SOT323	4 mm pitch, 8 mm tape and reel	-115 -	-	-135
BC847AW					
BC847BW					
BC847CW					
BC847T	SOT416	4 mm pitch, 8 mm tape and reel	-115 -	-	-135
BC847AT					
BC847BT					
BC847CT					
BC847AM	SOT883	2 mm pitch, 8 mm tape and reel	-	-	-315
BC847BM					
BC847CM					

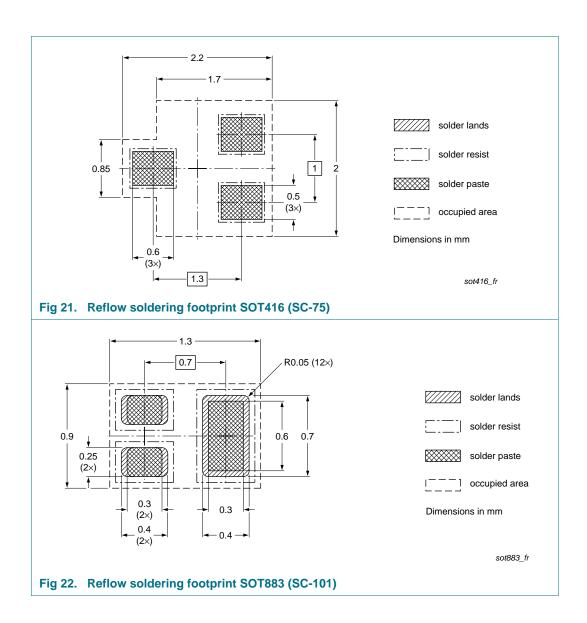
<sup>[1]</sup> For further information and the availability of packing methods, see <u>Section 13</u>.

<sup>[2]</sup> Valid for all available selection groups.

# 10. Soldering







NXP Semiconductors

BC847 series

45 V, 100 mA NPN general-purpose transistors

# 11. Revision history

### Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes	
BC847_SER v.8	20120820	Product data sheet	-	BC847_BC547_SER v.7	
Modifications:	<ul> <li>Type numbers removed: BC847B/DG, BC847BW/DG, BC847AT/DG, BC857, BC857B and BC857C</li> </ul>				
	<ul> <li>Section 12 "Legal information": updated</li> </ul>				
BC847_BC547_SER v.7	20081210	Product data sheet	-	BC847_BC547_SER v.6	
BC847_BC547_SER v.6	20050519	Product data sheet	-	-	

NXP Semiconductors BC847 series

#### 45 V, 100 mA NPN general-purpose transistors

# 12. Legal information

#### 12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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NXP Semiconductors

BC847 series

### 45 V, 100 mA NPN general-purpose transistors

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**BC847** series

## 45 V, 100 mA NPN general-purpose transistors

## 14. Contents

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Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.